Amendments to Claims

1-17 (cancelled)

18. (currently amended) The method as recited in Claim 17 26 wherein said layer of material is photochemically sensitive glass and wherein said substrate surface is glass, and wherein the physical properties of said layer of material are compatible with the physical properties of said substrate surface.

19. (currently amended) The method as recited in Claim 47 26 wherein said layer of material is photochemically insensitive glass and wherein said substrate surface is glass, and wherein the physical properties of said layer of material are compatible with the physical properties of said substrate surface.

20. (currently amended) The method as recited in Claim 47 26 wherein attaching said layer of material onto said substrate surface further comprises performing a diffusion bonding process thereon.

21. (currently amended) The method as recited in Claim 47 26 wherein attaching said layer of material onto said substrate surface further comprises performing a thin film sealing glass process thereon.

22. (currently amended) The method as recited in Claim 17 26 further comprises blackening a surface of said layer of material, such that said blackened

CDST-C169.CIP Examiner: Nguyen, T. surface of said layer of material is interposed between said layer of material and said substrate surface when said layer of material is disposed upon said substrate.

23. (currently amended) The method as recited in Claim 17 26 further

comprises blackening a surface of said substrate surface, such that said blackened

surface of said substrate surface is interposed between said layer of material and

said substrate surface when said layer of material is disposed upon said substrate

surface.

24. (currently amended) The method as recited in Claim 17 26 wherein

forming said layer of material further comprises performing a photolithographic

process thereon.

25. (currently amended) The method as recited in Claim 17 26 wherein

treating said layer of material further comprises applying an elevated

temperature to said layer of material and said substrate structure.

26. (currently amended) <u>A method of fabricating a support structure</u>

comprising:

attaching a layer of material onto a substrate surface, said layer of

material adaptable as said support structure;

forming said layer of material into said support structure;

treating said layer of material; and

etching said layer of material, such that said support structure is implementable during assembly of a display device; The method as recited in Claim 17 wherein etching further comprises sandblasting said layer of material with frozen particles of carbon dioxide, such that said substrate surface to which said layer of material is attached is unaffected by said sandblasting, when said layer of material is photochemically insensitive glass.

27. (currently amended) <u>A method of fabricating a support structure</u> comprising:

attaching a layer of material onto a substrate surface, said layer of material adaptable as said support structure;

forming said layer of material into said support structure;

treating said layer of material; and

etching said layer of material, such that said support structure is implementable during assembly of a display device; The method as recited in Claim 17 wherein etching said layer of material further comprises chemically washing said layer of material, such that said substrate surface is unaffected by said chemical washing when said layer of material is attached to said substrate surface prior to said washing, when said layer of material is photochemically sensitive glass.

28. (currently amended) The method as recited in Claim 47 26 wherein said substrate surface is an anode faceplate of said display device, and wherein

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Serial No.: 09/993,740 Group Art Unit: 3644 said support structure is interposed between said anode faceplate and a cathode back plate of said display device.

29. (currently amended) The method as recited in Claim 17 26 wherein said substrate surface is a cathode back plate of said display device, and wherein said support structure is interposed between said cathode back plate and an anode faceplate of said display device.

30. (currently amended) The method as recited in Claim 17 26 wherein said display device is an field emission display.

31-57 (cancelled)

58. (new) The method as recited in Claim 27 wherein said layer of material is photochemically sensitive glass and wherein said substrate surface is glass, and wherein the physical properties of said layer of material are compatible with the physical properties of said substrate surface.

59. (new) The method as recited in Claim 27 wherein said layer of material is photochemically insensitive glass and wherein said substrate surface is glass, and wherein the physical properties of said layer of material are compatible with the physical properties of said substrate surface.

CDST-C169.CIP Examiner: Nguyen, T. 60. (new) The method as recited in Claim 27 wherein attaching said layer

of material onto said substrate surface further comprises performing a diffusion

bonding process thereon.

61. (new) The method as recited in Claim 27 wherein attaching said layer

of material onto said substrate surface further comprises performing a thin film

sealing glass process thereon.

62. (new) The method as recited in Claim 27 further comprises blackening

a surface of said layer of material, such that said blackened surface of said layer

of material is interposed between said layer of material and said substrate

surface when said layer of material is disposed upon said substrate.

63. (new) The method as recited in Claim 27 further comprises blackening

a surface of said substrate surface, such that said blackened surface of said

substrate surface is interposed between said layer of material and said substrate

surface when said layer of material is disposed upon said substrate surface.

64. (new) The method as recited in Claim 27 wherein forming said layer

of material further comprises performing a photolithographic process thereon.

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The Examiner is invited to contact Applicants' undersigned representative if the Examiner believes such action would expedite resolution of the present application.

Respectfully submitted,

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